# Transistors 2SC839

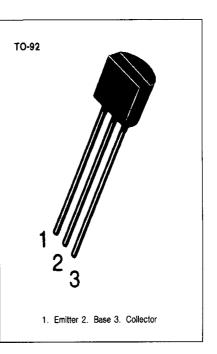


### FM/AM RADIO RF AMP, CONV, OSC, IF AMP

• Current-Gain-Bandwidth Product f<sub>T</sub> = 200MHz

# ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit	
Collector-Base Voltage	V <sub>CBO</sub>	35	٧	
Collector-Emitter Voltage	V <sub>CEO</sub>	30	V	
Emitter-Base Voltage	V <sub>EBO</sub>	4	V	
Collector Current	l <sub>c</sub>	100	mA	
Collector Dissipation	P <sub>C</sub>	250	mW	
Junction Temperature	Ti	150	•€	
Storage Temperature	Tstg	-55~150	°C	



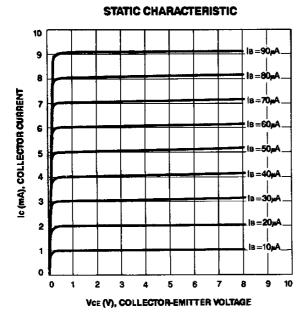
## **ELECTRICAL CHARACTERISTICS (Ta=25°C)**

Characteristic	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	$I_{C} = 100 \mu A, I_{E} = 0$	35			v
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	$I_C = 5mA$ , $I_B = 0$	30			V
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	$l_E = 10 \mu A, l_C = 0$	4			V
Collector Cut-off Current	Iceo	$V_{CB} = 30V, I_{E} = 0$			0.1	μА
Emitter Cut-off Current	I <sub>EBO</sub>	$V_{EB} = 4V$ , $I_{C} = 0$			0.1	μΑ
DC Current Gain	h <sub>FE</sub>	$V_{CE} = 12V, I_{C} = 2mA$	40		400	'
Base-Emitter On Voltage	V <sub>BE</sub> (on)	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	0.65	0.70	0.75	l v
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		0.1	0.4	V
Current Gain-Bandwidth Product	f	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA	80	200		MHz
Output Capacitance	Cob	$V_{CB} = 10V, I_{E} = 0$ f=1MHz		2.0	3.5	pF

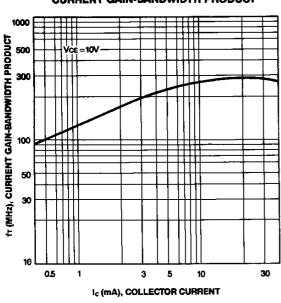
### **h**<sub>FE</sub> CLASSIFICATION

Classification	R	0	Υ	G
h <sub>FE</sub>	40-80	70-140	120-240	200-400

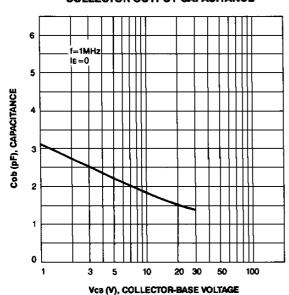




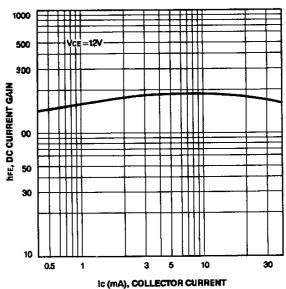
### **CURRENT GAIN-BANDWIDTH PRODUCT**



### **COLLECTOR OUTPUT CAPACITANCE**



### DC CURRENT GAIN



# BASE-EMITTER SATURATION VOLTAGE COLLECTOR-EMITTER SATURATION VOLTAGE

